

What is claim d is:

1. A dual damascene process for forming a multi-layer low-k interconnects, comprising the steps of:

5 depositing a first dielectric layer of a first low-k on a substrate;

etching said first dielectric layer for forming two dual damascene vias extending through said first dielectric layer to expose a surface of said substrate;

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forming a first barrier layer for covering on said first dielectric layer and said surface;

formulating two Cu conductor plugs each filled in one of said two dual damascene vias;

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forming a second barrier layer for covering on said two Cu conductor plugs to enclose said two Cu conductor plugs by said first and second barrier layers;

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etching-back said first dielectric layer for forming a trench between said two dual damascene vias; and spinning-on a second dielectric layer of a second low-k smaller than said first low-k in said trench.

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2. The process of claim 1, wherein said forming two Cu conductor plugs comprises the steps of:

depositing a Cu conductor layer filled in said two dual
damascene vias; and
etching-back said Cu conductor layer for leaving said
Cu conductor layer in said two dual damascene
vias.

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3. The process of claim 2, further comprising etching
said first barrier layer for leaving said first barrier layer in said
two dual damascene vias after said etching-back said Cu
conductor layer.

4. The process of claim 1, wherein said forming a
second barrier layer comprises the steps of:

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depositing said second barrier layer on said two Cu
conductor plugs and first dielectric layer; and
applying CMP to said second barrier layer for leaving
said second barrier layer over said two dual
damascene vias.

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5. The process of claim 1, wherein said depositing a
first dielectric layer comprises depositing a SiOC by CVD.

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6. The process of claim 1, wherein said etching-back
said first dielectric layer comprises wet etching said first
dielectric layer.

7. The process of claim 1, further comprising etching-back said second dielectric layer for planarizing said second dielectric layer to said second dielectric layer.

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8. The process of claim 7, further comprising the steps of:

depositing a third dielectric layer of a third low-k on said second dielectric and barrier layers;

10 etching said third dielectric and second barrier layers for forming two second dual damascene vias extending through said third dielectric and second barrier layers to expose a surface of said two Cu conductor plugs;

15 forming a third barrier layer for covering on said third dielectric layer and surface of said two Cu conductor plugs;

forming two second Cu conductor plugs each filled in one of said first two dual damascene vias;

20 forming a fourth barrier layer for covering on said two second Cu conductor plugs to enclose said two second Cu conductor plugs by said third and fourth barrier layers;

25 etching-back said third dielectric layer for forming a second trench between said two second dual

damascene vias; and
spinning-on a fourth dielectric layer of a fourth low-k
smaller than said third low-k in said second
trench.

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9. A multi-layer low-k dual damascene interconnect
comprising:

a first dielectric layer of a first low-k on a substrate;
a second dielectric layer of a second low-k smaller than
10 said first low-k spun-on said first dielectric layer;
a plurality of dual damascene vias formed in said first
and second dielectric layers;
a plurality of Cu conductor plugs each filled in one of
 said plurality of dual damascene vias; and
15 a barrier layer inserted between said plurality of Cu
 conductor plugs and first and second dielectric
 layers.

10. The interconnect of claim 9, wherein said first
20 low-k has a value between 2.5 and 3.

11. The interconnect of claim 9, wherein said first
dielectric layer comprises SiOC.

25 12. The interconnect of claim 9, wherein said second

low-k has a value smaller than 2.5.